

LCQ7853S5-N/M/P

AlGaAs Laser Diode

Ver.2 2004

◆ OVERVIEW

LCQ7853S5-N/M/P is a MOCVD grown 780nm band AlGaAs laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 3mW for Laser Beam Printer, industrial optical module and sensor application

◆ APPLICATION

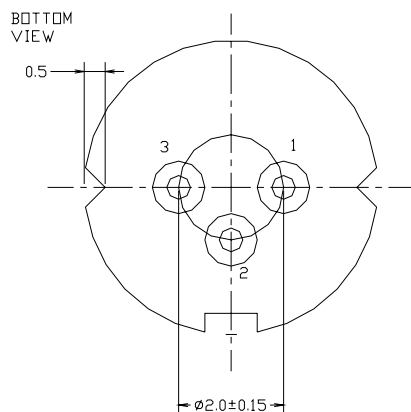
- Laser Beam Printer
- Sensor

◆ FEATURES

- Visible Light Output : $\lambda_p = 780 \text{ nm}$
- Optical Power Output : 3mW CW
- Package Type : TO-18 (5.6mm ϕ)
- Built-in Photo Diode for Monitoring Laser Diode

◆ ELECTRICAL CONNECTION

Bottom View



Pin Configuration

A	LD cathode, PD anode (Fig. 1)
B	LD , PD anode (Fig. 2)
C	LD anode, PD cathode (Fig. 3)

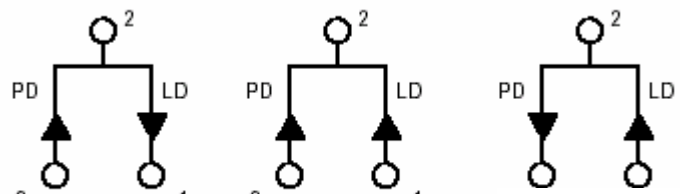


Fig. 1

Fig. 2

Fig. 3

LCQ7853S5-N

LCQ7853S5-M

LCQ7853S5-P

◆ **ABSOLUTE MAXIMUM RATING at Tc=25°C**

Item Sy	mbols	Values	Unit
Optical Output Power	P	5	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	25	V
Operating Temperature	Topr	-10 ~ +60	°C
Storage Temperature	Tstg	-40 ~ +85	°C

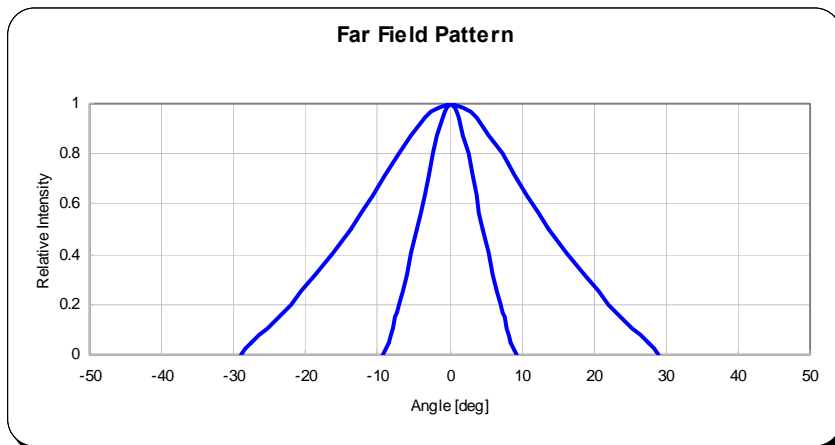
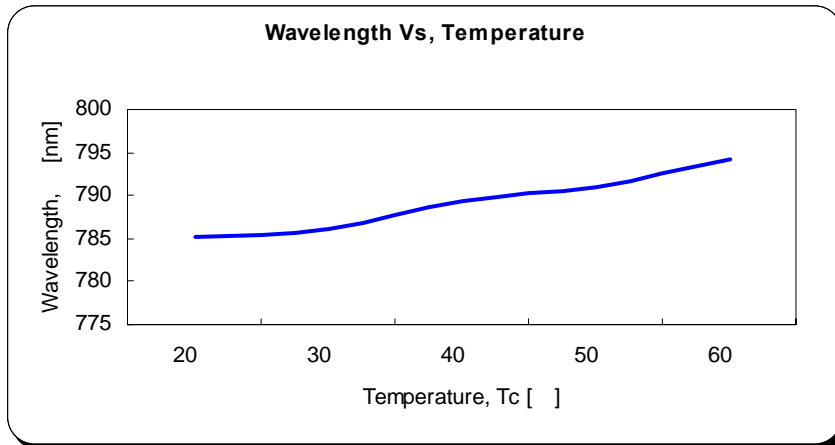
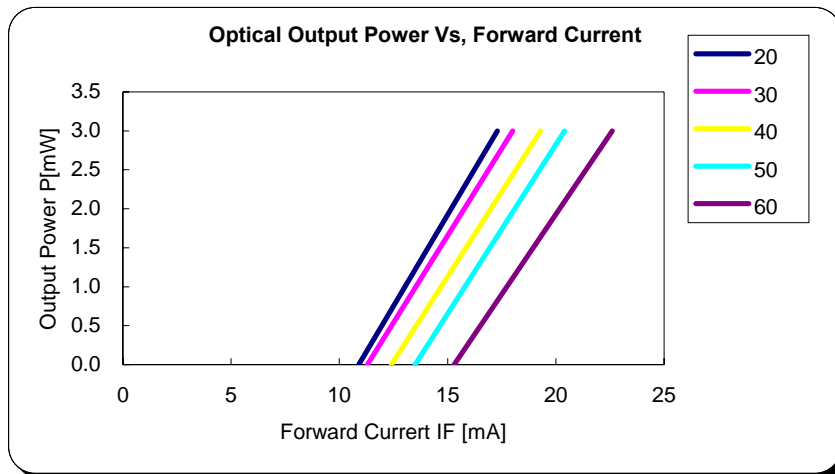
◆ **ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C**

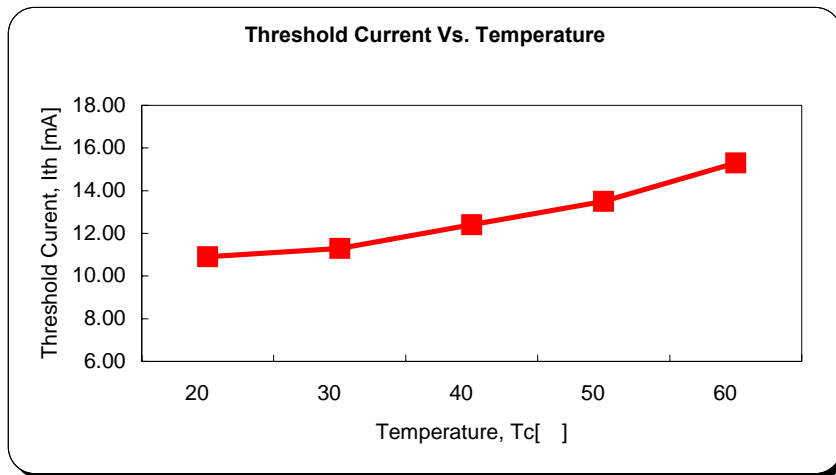
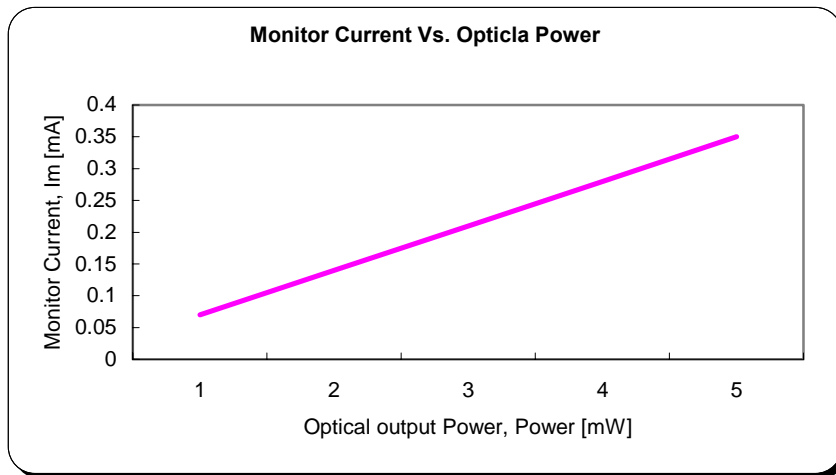
Items S	ymbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	3	-	mW	-
Threshold Current	Ith	8	13	20	mA	-
Operating Current	Iop	-	20	33	mA	Po=3mW
Operating Voltage	Vop	-	1.9	2.5	V	Po=3mW
Slope Efficiency	SE	-	0.4	0.5	mW/mA	2mW/(3mW)-(1mW)
Lasing Wavelength	λ_p	770	785	795	nm	Po=3mW
Beam Divergence	$\theta_{ }$	8	10	12	deg	Po=3mW
	θ_{\perp}	26	28	30	deg	Po=3mW
Beam Angle	$\Delta\theta_{ }$	-	-	±2.0	deg	Po=3mW
	$\Delta\theta_{\perp}$	-	-	±3.0	deg	Po=3mW
Monitor Current	Im	0.15	0.25	0.45	mA	Po=3mW
Optical Distance	$\Delta X, \Delta Y, \Delta Z$	-	-	±80	μm	Po=3mW
Astigmatism	As		5	10	μm	Po=3mW
Droop	ΔP		5	10	%	Po=3mW

NOTICE : LCQ7853S5-N/M/P to be operated on APC

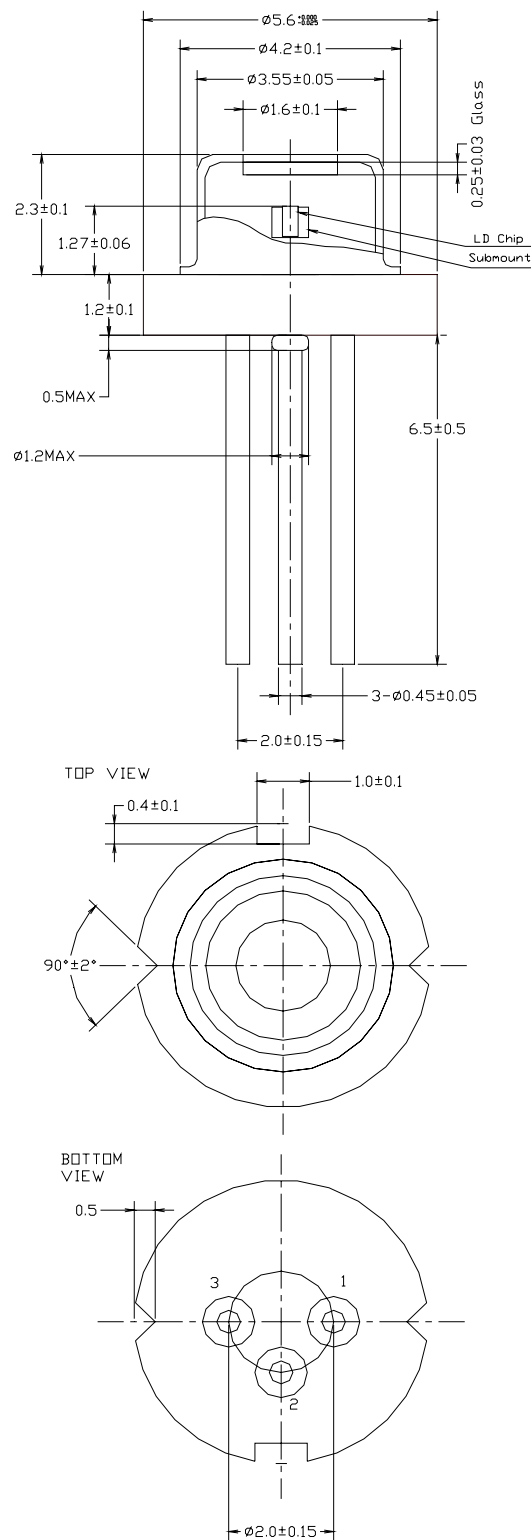
The above product specifications are subject to change without notice.

◆EXAMPLE of PRESENTATIVE CHARACTERISTICS





◆ PACKAGE DIMENSION



◆ PACKING

